

IPP65R225C7XKSA1

IPP65R225C7XKSA1 Information



For Reference Only

Part Number IPP65R225C7XKSA1

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 11A TO-220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IPP65R225C7XKSA1 Specifications

Manufacturer Part Number IPP65R225C7XKSA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series CoolMOS? C7 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 11A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 240µA Gate Charge (Qg) (Max) @ Vgs 20nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 996pF @ 400V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 63W (Tc) Rds On (Max) @ Id, Vgs 225 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3 Report errors? Report errors?		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 240μAGate Charge (Qg) (Max) @ Vgs20nC @ 10VInput Capacitance (Ciss) (Max) @ Vds996pF @ 400VVgs (Max)±20VFET Feature-Power Dissipation (Max)63W (Tc)Rds On (Max) @ Id, Vgs225 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 240μAGate Charge (Qg) (Max) @ Vgs20nC @ 10VInput Capacitance (Ciss) (Max) @ Vds996pF @ 400VVgs (Max)±20VFET Feature-Power Dissipation (Max)63W (Tc)Rds On (Max) @ Id, Vgs225 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Series	CoolMOS? C7
Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 240μAGate Charge (Qg) (Max) @ Vgs20nC @ 10VInput Capacitance (Ciss) (Max) @ Vds996pF @ 400VVgs (Max)±20VFET Feature-Power Dissipation (Max)63W (Tc)Rds On (Max) @ Id, Vgs225 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Capacitance (Ciss) (Max) @ Vds 225 mOhm @ 4.8A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 240μAGate Charge (Qg) (Max) @ Vgs20nC @ 10VInput Capacitance (Ciss) (Max) @ Vds996pF @ 400VVgs (Max)±20VFET Feature-Power Dissipation (Max)63W (Tc)Rds On (Max) @ Id, Vgs225 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id 4V @ 240μA Gate Charge (Qg) (Max) @ Vgs 20nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 996pF @ 400V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 63W (Tc) Rds On (Max) @ Id, Vgs 225 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	11A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 996pF @ 400V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 225 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 996pF @ 400V Vgs (Max) E20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 225 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 240μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)63W (Tc)Rds On (Max) @ Id, Vgs225 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	20nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	996pF @ 400V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 225 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs225 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Power Dissipation (Max)	63W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	225 mOhm @ 4.8A, 10V
Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

IPP65R225C7XKSA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPP65R225C7XKSA1 Payment Methods



















IPP65R225C7XKSA1 Shipping Methods













If you have any question about IPP65R225C7XKSA1, please do not hesitate to contact us!

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